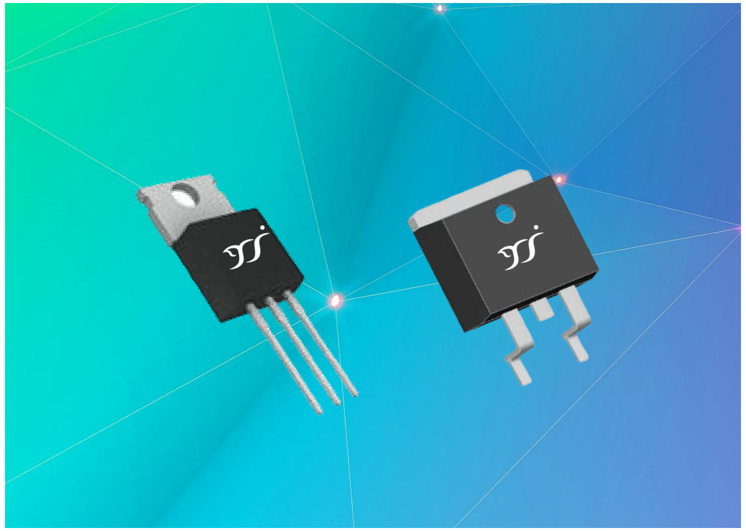
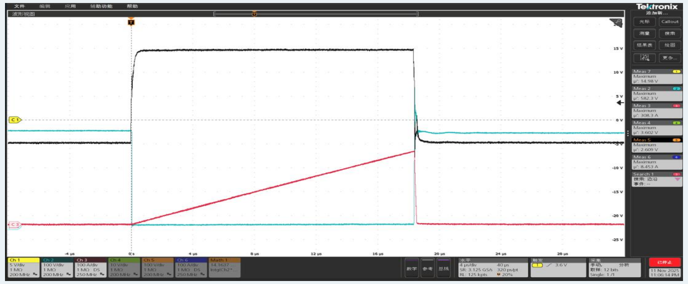
新 品
发 布

微沟槽IGBT 650V单管——让大电流应用“轻装上阵”



产 品
特 点

1. 精细微沟槽工艺平台，极具性价比的芯片方案；
2. 电压等级为650V，电流等级为50A@Tc=100℃ ；
3. 低导通损耗，适用于大电流应用领域；
4. 具有较强的通流能力，Icm可达300A



如左图所示为器件300A单脉冲关断波形

Product Name	V_{CES} (V)	Ic(A)	$V_{GE(th)}$ (V)	$V_{CE(sat)}$ (V)	VF(V)	Pd(W)	Tj（℃）
DGP50N65ATS2A	650V	50A	4.8	1.4	-	283	-40~175
DGB50N65ATS2A	650V	50A	4.8	1.4	-	283	-40~175

更多产品详见官网

产品介绍

扬杰科技近日推出了新一代TO-220/TO-263封装650V IGBT单管，产品采用新一代微沟槽工艺平台，极大的优化了器件的导通损耗，产品参数一致性好，可靠性优良。并且器件的导通压降低，通流能力极强，适用于脱毛仪这类对通流能力要求高的应用领域。

典 型
应 用

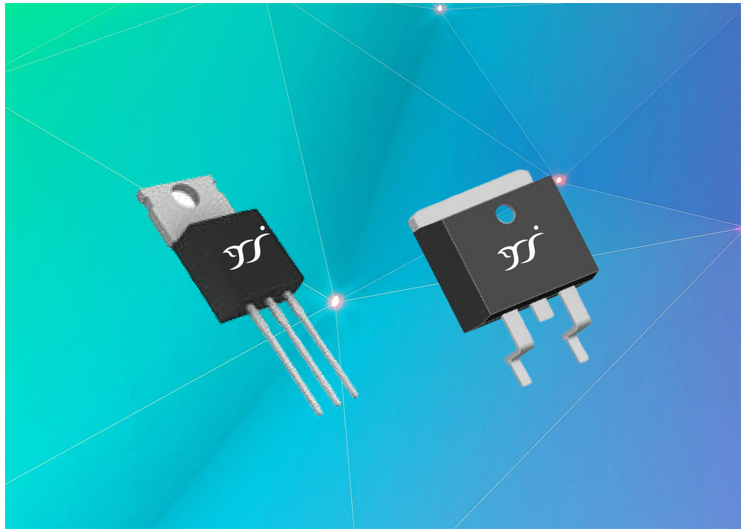
脱毛仪

新品发布

扬杰科技
YANGJIE TECHNOLOGY

NEW PRODUCT

Micro-pattern Trenches IGBT for Hair Removal Device



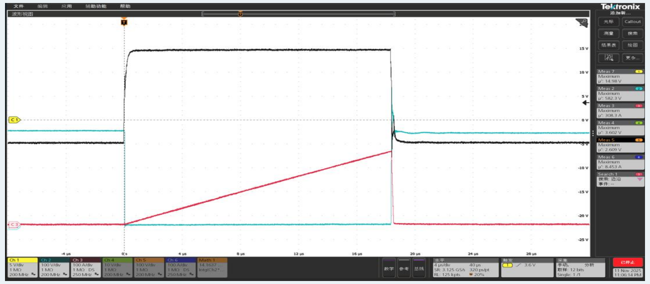
Product Introduction

Yangjie Technology recently launched a new generation of TO-220/TO-263 packages 650V discrete IGBT. The products adopt a new generation of micro-trench process platform, greatly optimizing the device's conduction loss. The products have good parameter consistency and excellent reliability. Moreover, the devices have reduced conduction voltage and strong current-carrying capability, making them suitable for applications such as hair removal devices that require high current capacity.

New Product Announcement

Product Features

1. Micro-trench process platform, a highly cost-effective chip solution;
2. Voltage rating of 650V, current rating of 50A@Tc=100℃;
3. Low conduction loss, suitable for high-current applications;
4. Strong current-carrying capability, with Icm up to 300A



As shown in the left figure, it is the single-pulse turn-off waveform of the 300A device.

Product Name	V_{CES} (V)	Ic(A)	$V_{GE(th)}$ (V)	$V_{CE(sat)}$ (V)	VF(V)	Pd(W)	Tj (℃)
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DGB50N65ATS2A	650V	50A	4.8	1.4	-	283	-40~175

Please refer to the official website for more products

Applica-tion

Hair removal device

扬杰科技
YANGJIE TECHNOLOGY